



No. 3527

VPM04F

**Video Pack, Three-channel,
RGB Video Output Amplifier
for Medium-resolution CRT Displays**

OVERVIEW

The VPM04F is a composite, three-channel, video output amplifier IC for medium-resolution RGB displays. It is fabricated using hybrid technology and incorporates high-precision FBET and LSBT transistors to provide high output voltages over a wide bandwidth with minimal external components. The dual-in-line metal package reduces EMI and simplifies circuit board design.

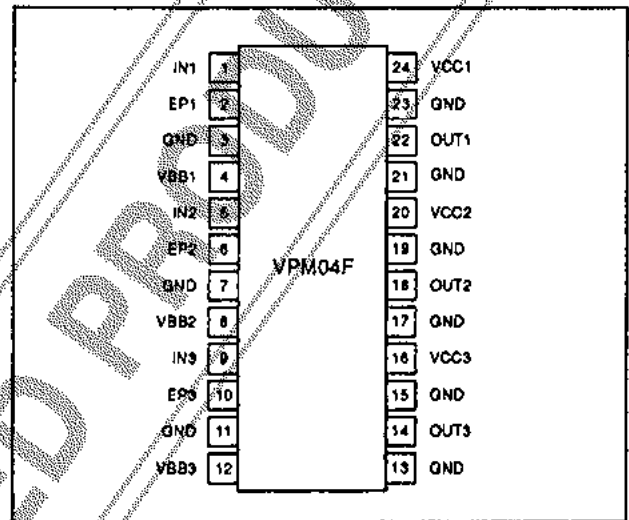
The VPM04F is ideally suited to medium-resolution RGB monitors which use a 39 kHz line frequency. Applications include EGA, VGA, MacII and television displays. The VPA05 and VPA07 single-channel amplifiers are recommended for monochrome applications.

The VPM04F operates from a 80 V supply (typ) and is available in 24-pin DIPs.

FEATURES

- Up to 40 V_{pp} output
- High-precision FBET and LSBT transistors
- 45 MHz bandwidth
- Metal case reduces EMI
- Dual-in-line package simplifies circuit board design
- Up to 120 V supply and 15 V bias
- 24-pin DIP

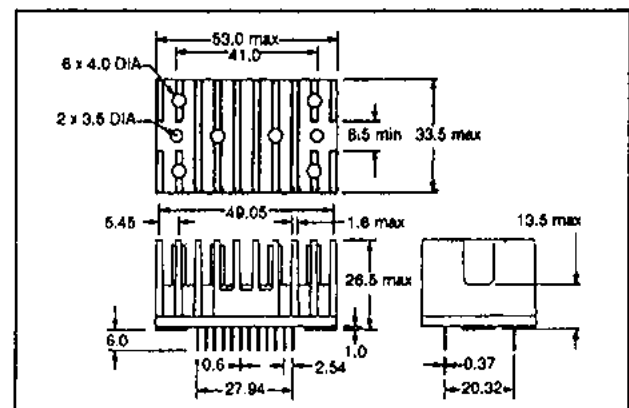
PINOUT



PACKAGE DIMENSIONS

Unit: mm

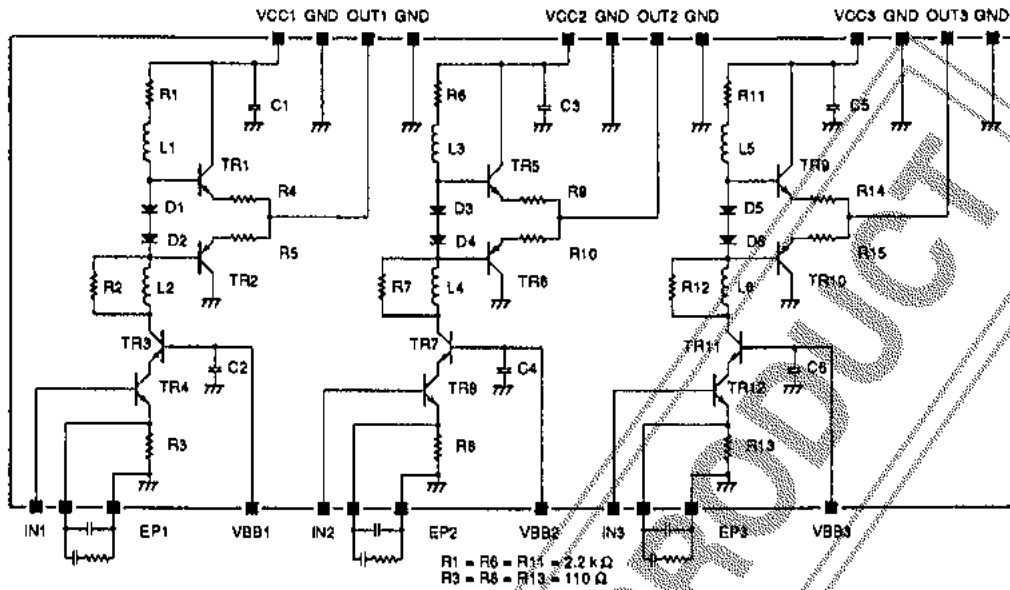
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DISCONTINUED PRODUCT

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INTERNAL CIRCUIT



PIN DESCRIPTION

Number	Name	Description
1	IN1	Channel 1 input
2	EP1	Channel 1 external peaking input
3, 7, 11, 13, 15, 17, 19, 21, 23	GND	Ground
4	VBB1	Channel 1 bias voltage
5	IN2	Channel 2 input
6	EP2	Channel 2 external peaking input
8	VBB2	Channel 2 bias voltage
9	IN3	Channel 3 input
10	EP3	Channel 3 external peaking input
12	VBB3	Channel 3 bias voltage
14	OUT3	Channel 3 output
16	VCC3	Channel 3 supply voltage
18	OUT2	Channel 2 output
20	VCC2	Channel 2 supply voltage
22	OUT1	Channel 1 output
24	VCC1	Channel 1 supply voltage

VPM04F

SPECIFICATIONS

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply voltage	V_{CC} max	120	V
Bias voltage	V_{BB} max	15	V
Power dissipation	P_D	15	W
Junction temperature	T_j	150	deg. C
Operating temperature	T_{opp}	85	deg. C
Storage temperature range	T_{stg}	-20 to 110	deg. C

Recommended Operating Conditions

$T_a = 25$ deg. C

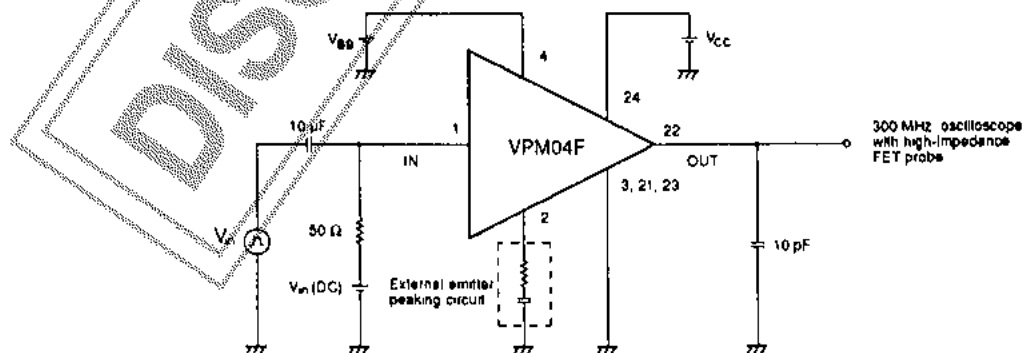
Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Supply voltage	V_{CC}	$V_{out} = 40$ V _{p-p} , $V_{in}(DC) = 2.5$ V	-	80	-	V
Bias voltage	V_{BB}		-	10	-	V

Electrical Characteristics

$T_a = 25$ deg. C

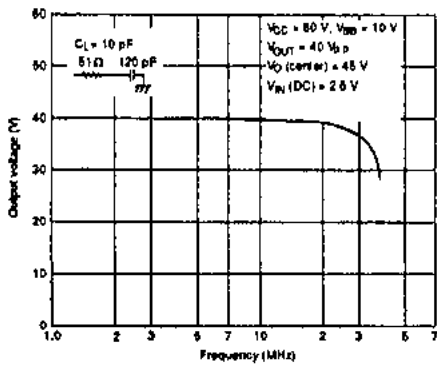
Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Frequency bandwidth	f_c (-3 dB)	$V_{out} = 40$ V _{p-p} , $V_{CC} = 80$ V, $V_{BB} = 10$ V, $V_{in}(DC) = 2.5$ V	-	45	-	MHz
Voltage gain	G_v		17	19	21	
Current consumption	I_{cc}	$f = 10$ MHz, $V_{CC} = 80$ V, $V_{BB} = 10$ V	-	22	-	mA
		$f = 45$ MHz, $V_{CC} = 80$ V, $V_{BB} = 10$ V	-	30	-	

Measurement Circuit

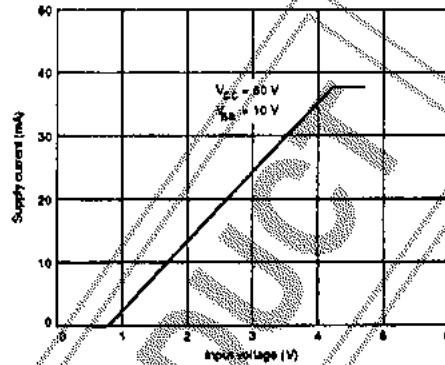


Typical Performance Characteristics

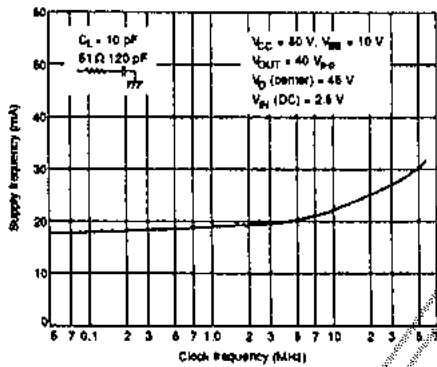
Output voltage vs. frequency



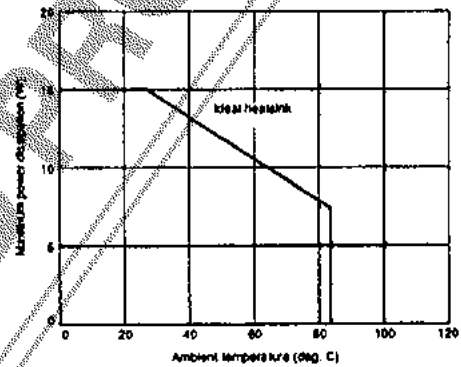
Supply current vs. DC Input voltage



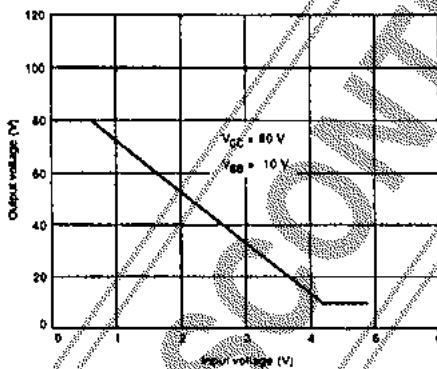
Supply current vs. frequency



Power dissipation vs. ambient temperature



Output voltage vs. DC Input voltage



HEATSINK DESIGN

The transistor junction temperature should be kept below 150 deg. C. To achieve this, heatsinks should be designed to keep the case temperature below 100 deg. C. The VPM04 is designed for use with an external heatsink whereas the VPM04F has a composite heatsink

package. The VPM04 heatsink should be designed according to its drive conditions as shown in table 1. The VPM04F maximum drive conditions are determined by the ambient temperature as shown in table 2.

VPM04F

Table 1. VPM04 recommended heatsink characteristics

Parameter	Symbol	Condition	Rating	Unit
Thermal resistance	θ_h	$V_{CC} = 80 \text{ V}$, $V_{BB} = 10 \text{ V}$, $V_{OUT} = 40 \text{ V}_{p-p}$, $f_c = 45 \text{ MHz}$, $T_a = 60 \text{ deg. C}$	8.8	deg. C/W
		$V_{CC} = 90 \text{ V}$, $V_{BB} = 10 \text{ V}$, $V_{OUT} = 50 \text{ V}_{p-p}$, $f_c = 45 \text{ MHz}$, $T_a = 40 \text{ deg. C}$	5.7	

Table 2. VPM04F recommended drive conditions

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	V_{CC}	$T_a = 60 \text{ deg. C}$	80	V
		$T_a = 40 \text{ deg. C}$	90	
Output voltage	V_{OUT}	$T_a = 60 \text{ deg. C}$	40	V_{p-p}
		$T_a = 40 \text{ deg. C}$	50	
Operating frequency	f_c	$T_a = 60 \text{ deg. C}$	45	MHz
		$T_a = 40 \text{ deg. C}$	45	

Note

Composite heatsink package. $\theta_h = 8.0 \text{ deg. C/W}$

The power dissipation versus supply voltage is shown in figure 1, and thermal resistance versus supply voltage, in figure 2.

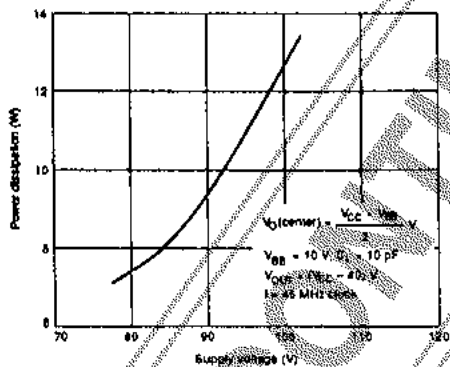


Figure 1. Power dissipation vs. supply voltage

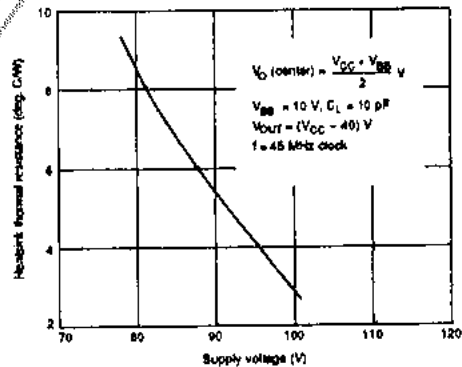


Figure 2. Thermal resistance vs. supply voltage

PRECAUTIONS

- Pins should not be short-circuited while power is applied.
- Correct heatsinking should be used to keep the case temperature below 100 deg. C.
- Note that the case is connected to ground.
- The recommended mounting torque is 4 to 6 kg/cm.

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